

ABSTRACT OF THE DISCLOSURE

An active region, a source region, and a drain region are formed on a single crystal semiconductor substrate or a single crystal semiconductor thin film. Impurity regions called pinning regions are formed in striped form in the active region so as to reach both
5 of the source region and the drain region. Regions interposed between the pinning regions serve as channel forming regions. A tunnel oxide film, a floating gate, a control gate, etc. are formed on the above structure. The impurity regions prevent a depletion layer from expanding from the source region toward the drain region.